

Short description

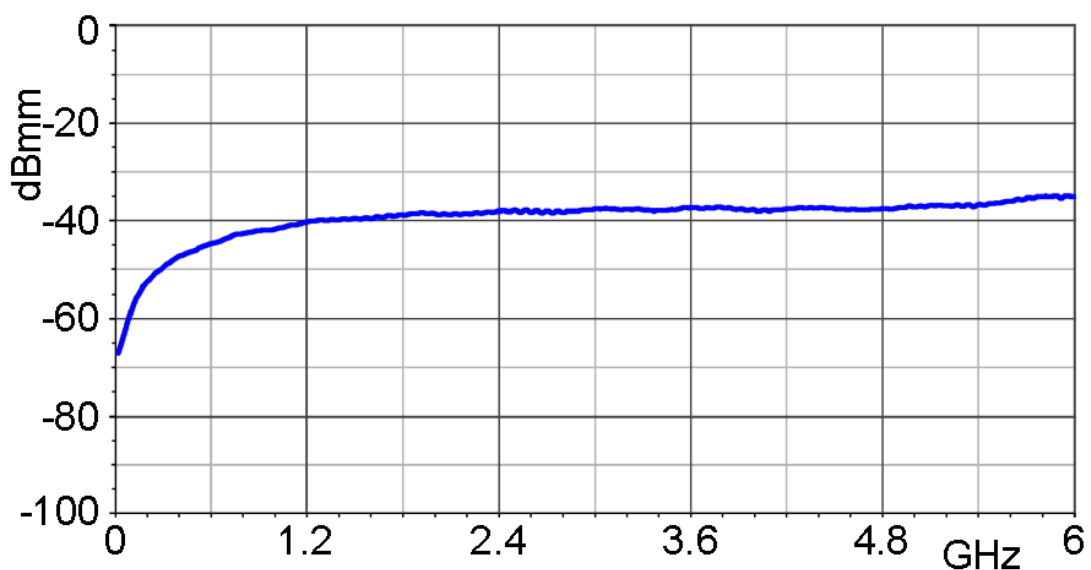
The electrode on the probe head of the XF-E 09s near-field probe detects electrical fields which, for example are decoupled above the IC's surface. The probe's resolution allows for measurements at a distance of 0.5 mm upto 10 mm above an assembly.

The XF-E 09s is a passive near-field probe. In principle it has the same structure as the XF-E 04s probe. To measure, the E-field probe is positioned above or onto components and printed circuit boards. It has a current attenuating sheath and, therefore, its upper half is electrically shielded. It can be connected to a spectrum analyzer or an oscilloscope with a 50 Ω input. The E-field probe has an internal terminating resistance.

Technical parameters

Frequency range	30 MHz ... 6 GHz
Probe head dimensions	$\approx (10 \times 10)$ mm
Connector - output	SMA, female, jack

Frequency response [dB μ V] / [dB μ V/mm]

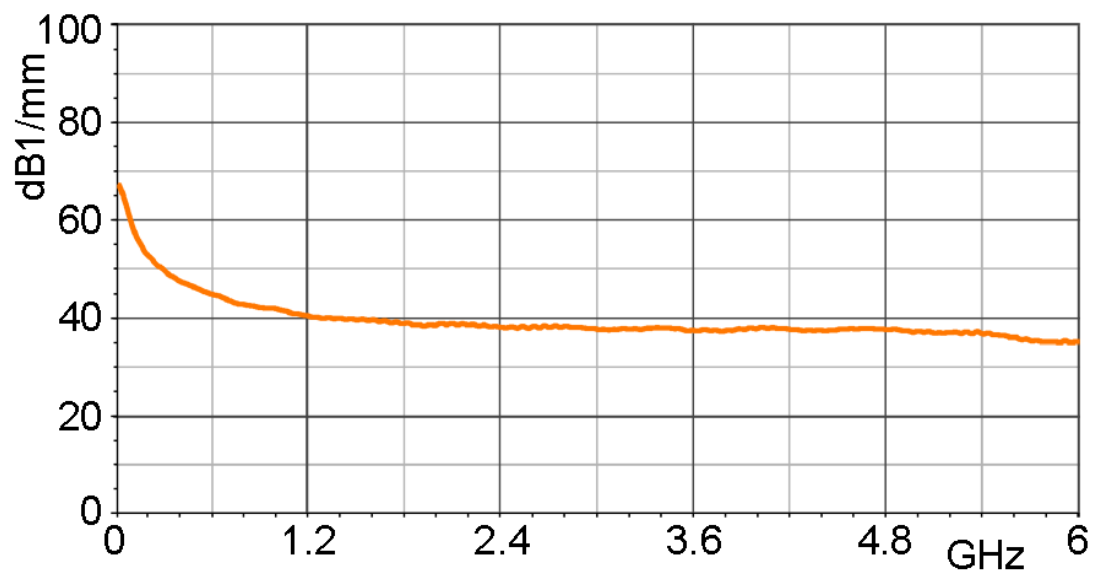


XF-E 09s

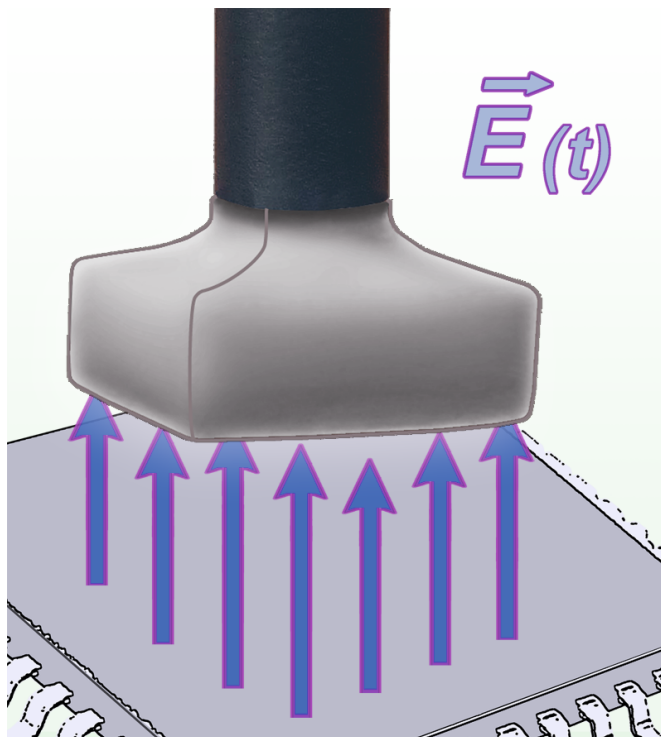
E-Field Probe 30 MHz up to 6 GHz

LANGER
EMV-Technik

E- field correction curve [dB μ V/mm] / [dB μ V]



Measuring principles



XF-E 09s

E-Field Probe 30 MHz up to 6 GHz

LANGER
EMV-Technik

Probe head

